International
IOR Rectifier

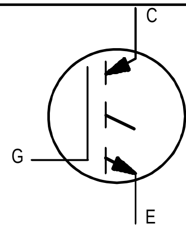
IRG4PH50K

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
UltraFast IGBT

Features

- High short circuit rating optimized for motor control, t_{sc} =10µs, V_{CC} = 720V, T_J = 125°C, V_{GE} = 15V
- Combines low conduction losses with high switching speed
- Latest generation design provides tighter parameter distribution and higher efficiency than previous generations



n-channel

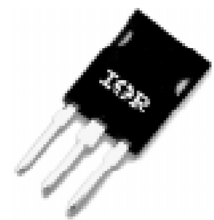
V_{CES} = 1200V

$V_{CE(on)\ typ.}$ = 2.77V

@V_{GE} = 15V, I_C = 24A

Benefits

- As a Freewheeling Diode we recommend our HEXFRED™ ultrafast, ultrasoft recovery diodes for minimum EMI/Noise and switching losses in the Diode and IGBT
- Latest generation 4 IGBTs offer highest power density motor controls possible
- This part replaces the IRGPH50K and IRGPH50M devices



TO-247 AB

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	45	A
I_C @ T_C = 100°C	Continuous Collector Current	24	
I_{CM}	Pulsed Collector Current ①	90	
I_{LM}	Clamped Inductive Load Current ②	90	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	±20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	190	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	200	W
P_D @ T_C = 100°C	Maximum Power Dissipation	78	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case	—	0.64	°C/W
$R_{θCS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{θJA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6 (0.21)	—	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage	18	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.91	—	V/°C	V_{GE} = 0V, I_C = 2.0mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.77	3.5	V	I_C = 24A, V_{GE} = 15V
		—	3.28	—		I_C = 45A, see figures 2, 5
		—	2.54	—		I_C = 24A , T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}$, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	$V_{CE} = V_{GE}$, I_C = 2.0mA
g_{fe}	Forward Transconductance	13	19	—	S	V_{CE} = 100 V, I_C = 24A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 1200V
		—	—	2.0		V_{GE} = 0V, V_{CE} = 10V, T_J = 25°C
		—	—	5000		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	180	270	nC	I_C = 24A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	25	38		V_{CC} = 400V, see figure 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	70	110		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	36	—	ns	T_J = 25°C
t_r	Rise Time	—	27	—		I_C = 24A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	—	200	300		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	130	190		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	1.21	—	mJ	see figures 9,10,14
E_{off}	Turn-Off Switching Loss	—	2.25	—		
E_{ts}	Total Switching Loss	—	3.46	4.1		
t_{sc}	Short Circuit Withstand Time	10	—	—	µs	V_{CC} = 720V, T_J = 125°C, V_{GE} = 15V, R_G = 5.0Ω
$t_{d(on)}$	Turn-On Delay Time	—	35	—	ns	T_J = 150°C,
t_r	Rise Time	—	29	—		I_C = 24A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	—	380	—		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	280	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	7.80	—	mJ	see figures 10,11,14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	2800	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	140	—		V_{CC} = 30V, see figure 7
C_{res}	Reverse Transfer Capacitance	—	53	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (see figure 13b)

② V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 10µH, R_G = 5.0Ω, (see figure 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

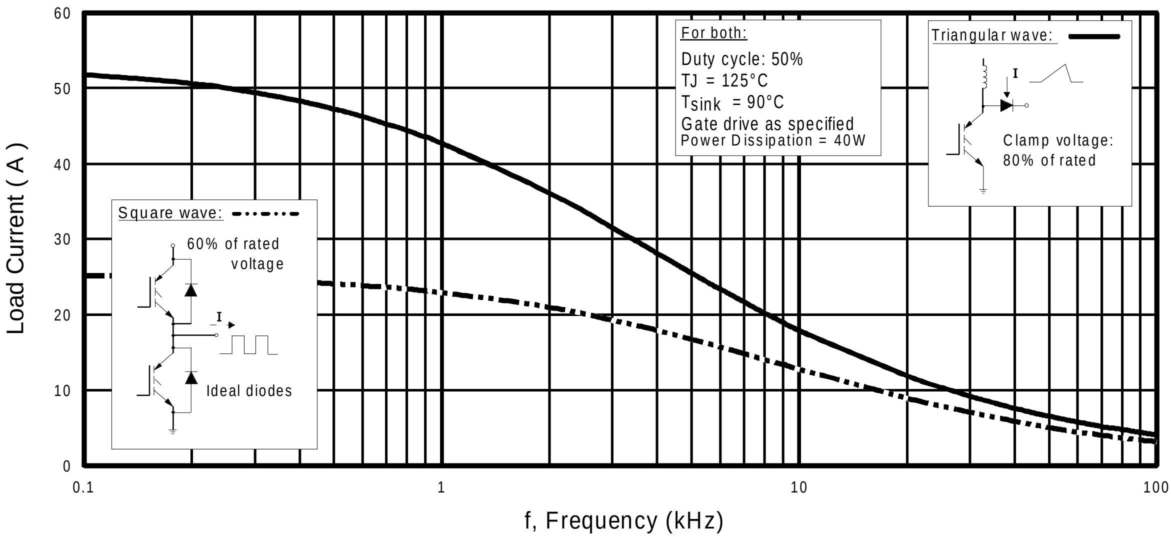


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

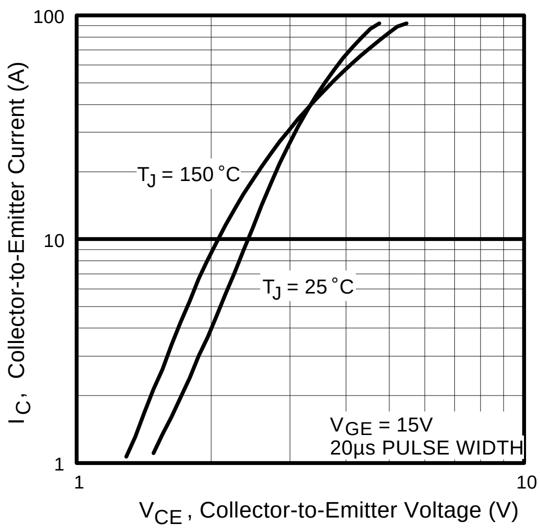


Fig. 2 - Typical Output Characteristics

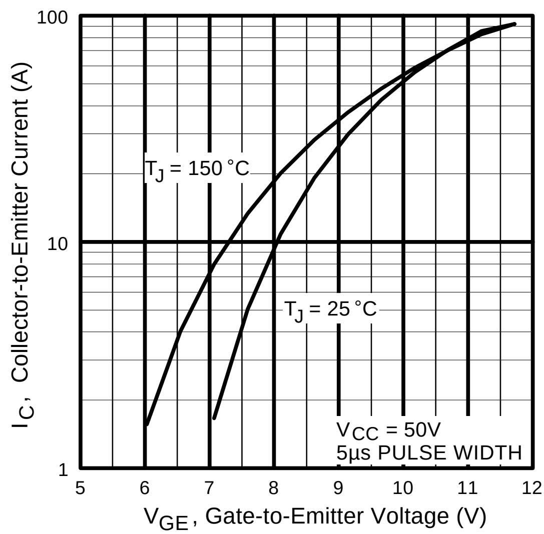


Fig. 3 - Typical Transfer Characteristics

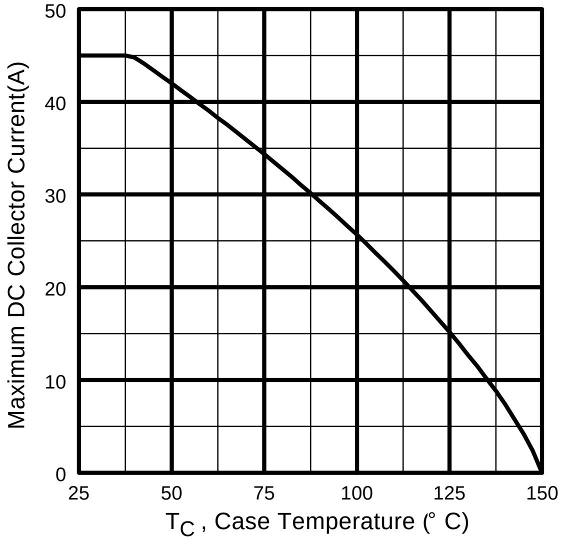


Fig. 4 - Maximum Collector Current vs. Case Temperature

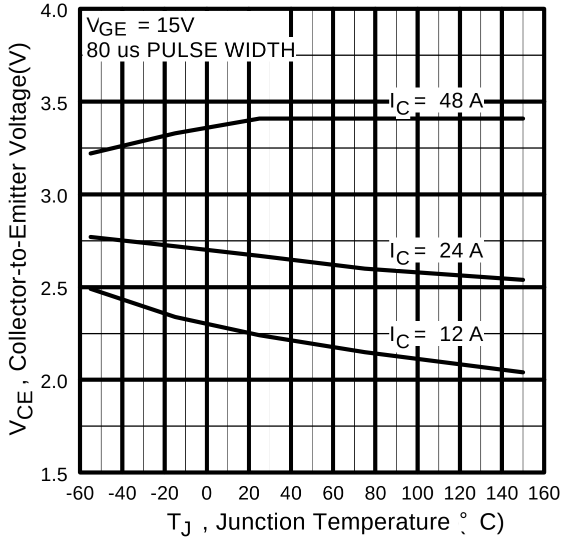


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

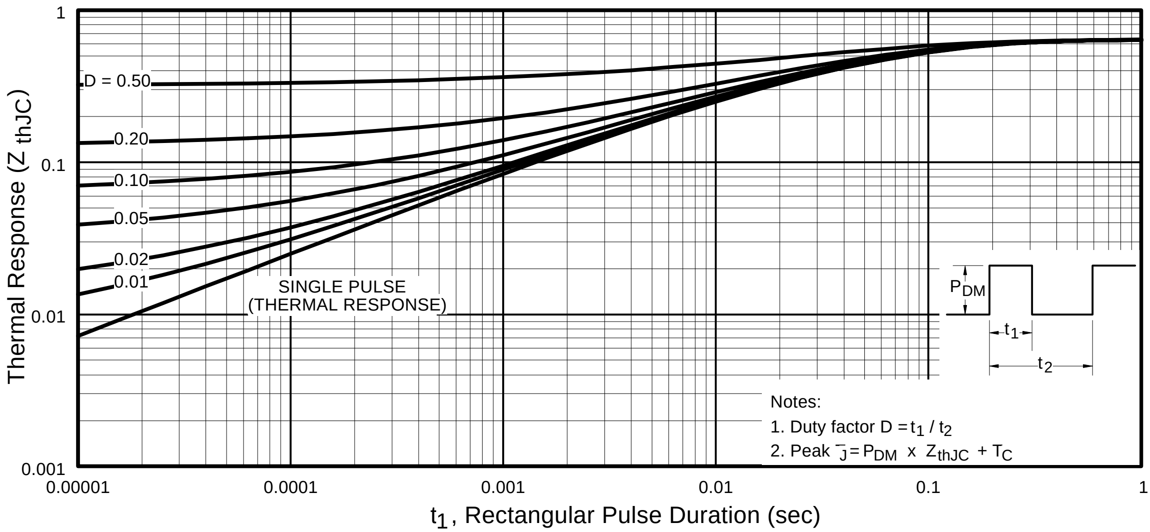


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

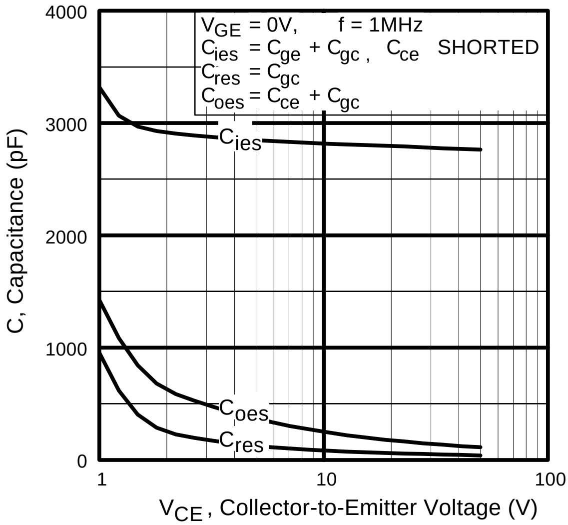


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

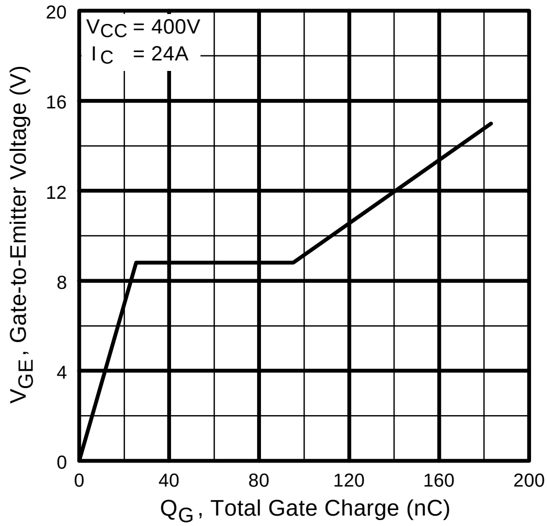


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

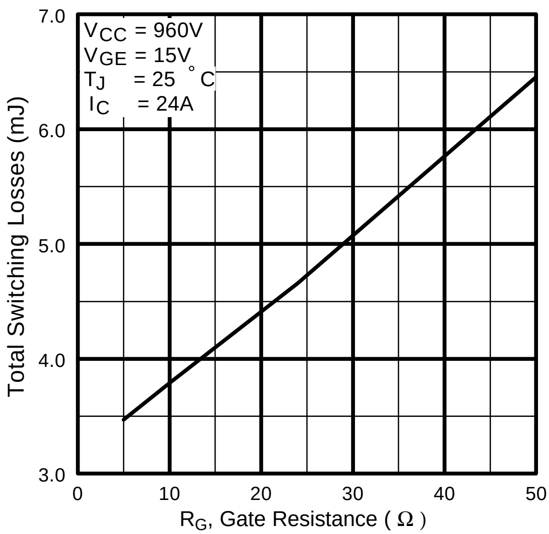


Fig. 9 - Typical Switching Losses vs. Gate Resistance

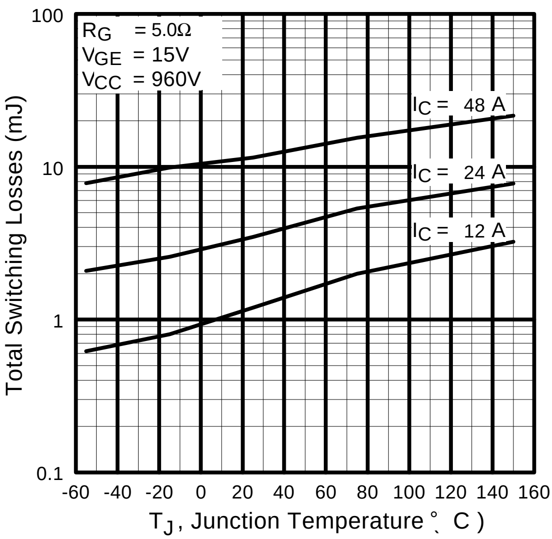


Fig. 10 - Typical Switching Losses vs. Junction Temperature

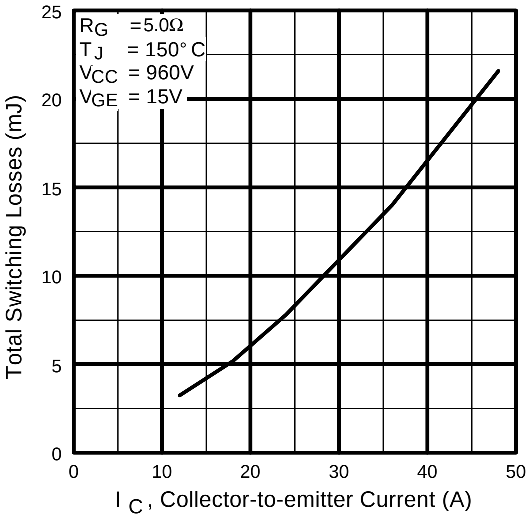


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

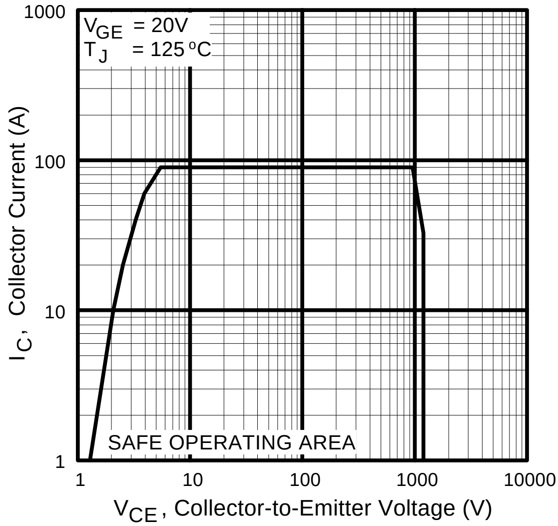


Fig. 12 - Turn-Off SOA